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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	11000
Number of Logic Elements/Cells	44000
Total RAM Bits	1990656
Number of I/O	118
Number of Gates	-
Voltage - Supply	1.045V ~ 1.155V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	285-LFBGA, CSPBGA
Supplier Device Package	285-CSFBGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe5u-45f-6mg285c

2. Architecture

2.1. Overview

Each ECP5/ECP5-5G device contains an array of logic blocks surrounded by Programmable I/O Cells (PIC). Interspersed between the rows of logic blocks are rows of sysMEM™ Embedded Block RAM (EBR) and rows of sysDSP™ Digital Signal Processing slices, as shown in Figure 2.1 on page 13. The LFE5-85 devices have three rows of DSP slices, the LFE5-45 devices have two rows, and both LFE5-25 and LFE5-12 devices have one. In addition, the LFE5UM/LFE5UM5G devices contain SERDES Duals on the bottom of the device.

The Programmable Functional Unit (PFU) contains the building blocks for logic, arithmetic, RAM and ROM functions. The PFU block is optimized for flexibility, allowing complex designs to be implemented quickly and efficiently. Logic Blocks are arranged in a two-dimensional array.

The ECP5/ECP5-5G devices contain one or more rows of sysMEM EBR blocks. sysMEM EBRs are large, dedicated 18 Kb fast memory blocks. Each sysMEM block can be configured in a variety of depths and widths as RAM or ROM. In addition, ECP5/ECP5-5G devices contain up to three rows of DSP slices. Each DSP slice has multipliers and adder/accumulators, which are the building blocks for complex signal processing capabilities.

The ECP5 devices feature up to four embedded 3.2 Gb/s SERDES channels, and the ECP5-5G devices feature up to four embedded 5 Gb/s SERDES channels. Each SERDES channel contains independent 8b/10b encoding / decoding, polarity adjust and elastic buffer logic. Each group of two SERDES channels, along with its Physical Coding Sublayer (PCS) block, creates a dual DCU (Dual Channel Unit). The functionality of the SERDES/PCS duals can be controlled by SRAM cell settings during device configuration or by registers that are addressable during device operation. The registers in every dual can be programmed via the SERDES Client Interface (SCI). These DCUs (up to two) are located at the bottom of the devices.

Each PIC block encompasses two PIOs (PIO pairs) with their respective sysI/O buffers. The sysI/O buffers of the ECP5/ECP5-5G devices are arranged in seven banks (eight banks for LFE5-85 devices in caBGA756 and caBGA554 packages), allowing the implementation of a wide variety of I/O standards. One of these banks (Bank 8) is shared with the programming interfaces. Half of the PIO pairs on the left and right edges of the device can be configured as LVDS transmit pairs, and all pairs on left and right can be configured as LVDS receive pairs. The PIC logic in the left and right banks also includes pre-engineered support to aid in the implementation of high speed source synchronous standards such as XGMII, 7:1 LVDS, along with memory interfaces including DDR3 and LPDDR3.

The ECP5/ECP5-5G registers in PFU and sysI/O can be configured to be SET or RESET. After power up and the device is configured, it enters into user mode with these registers SET/RESET according to the configuration setting, allowing the device entering to a known state for predictable system function.

Other blocks provided include PLLs, DLLs and configuration functions. The ECP5/ECP5-5G architecture provides up to four Delay-Locked Loops (DLLs) and up to four Phase-Locked Loops (PLLs). The PLL and DLL blocks are located at the corners of each device.

The configuration block that supports features such as configuration bit-stream decryption, transparent updates and dual-boot support is located at the bottom of each device, to the left of the SERDES blocks. Every device in the ECP5/ECP5-5G family supports a sysCONFIG™ ports located in that same corner, powered by Vccio8, allowing for serial or parallel device configuration.

In addition, every device in the family has a JTAG port. This family also provides an on-chip oscillator and soft error detect capability. The ECP5 devices use 1.1 V and ECP5UM5G devices use 1.2 V as their core voltage.

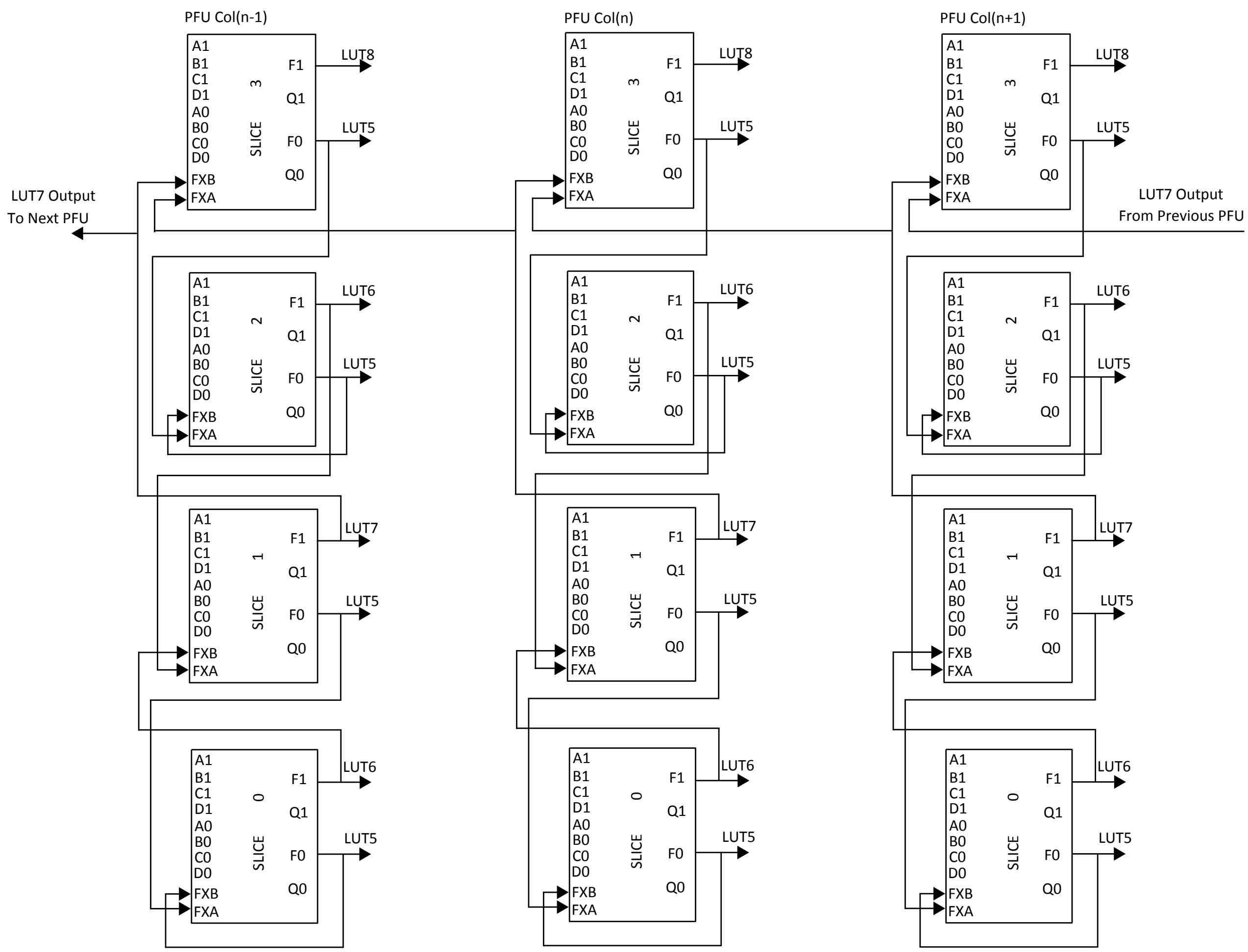


Figure 2.4. Connectivity Supporting LUT5, LUT6, LUT7, and LUT8

Table 2.2. Slice Signal Descriptions

Function	Type	Signal Names	Description
Input	Data signal	A0, B0, C0, D0	Inputs to LUT4
Input	Data signal	A1, B1, C1, D1	Inputs to LUT4
Input	Multi-purpose	M0	Multipurpose Input
Input	Multi-purpose	M1	Multipurpose Input
Input	Control signal	CE	Clock Enable
Input	Control signal	LSR	Local Set/Reset
Input	Control signal	CLK	System Clock
Input	Inter-PFU signal	FCI	Fast Carry-in[1]
Input	Inter-slice signal	FXA	Intermediate signal to generate LUT6, LUT7 and LUT8[2]
Input	Inter-slice signal	FXB	Intermediate signal to generate LUT6, LUT7 and LUT8[2]
Output	Data signals	F0, F1	LUT4 output register bypass signals
Output	Data signals	Q0, Q1	Register outputs
Output	Inter-PFU signal	FCO	Fast carry chain output[1]

Notes:

1. See Figure 2.3 on page 15 for connection details.
2. Requires two adjacent PFUs.

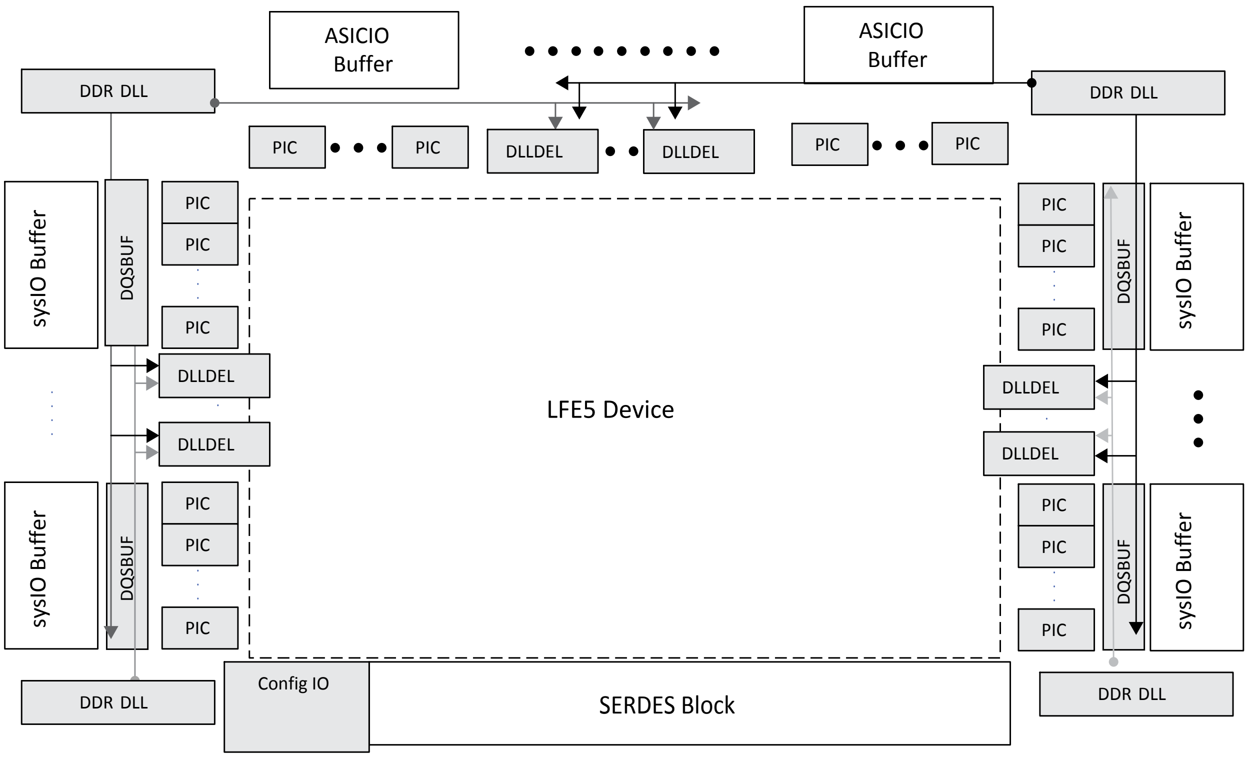


Figure 2.11. ECP5/ECP5-5G DLL Top Level View (For LFE-45 and LFE-85)

2.8. sysMEM Memory

ECP5/ECP5-5G devices contain a number of sysMEM Embedded Block RAM (EBR). The EBR consists of an 18 Kb RAM with memory core, dedicated input registers and output registers with separate clock and clock enable. Each EBR includes functionality to support true dual-port, pseudo dual-port, single-port RAM, ROM and FIFO buffers (via external PFUs).

2.8.1. sysMEM Memory Block

The sysMEM block can implement single port, dual port or pseudo dual port memories. Each block can be used in a variety of depths and widths as listed in Table 2.6 on page 25. FIFOs can be implemented in sysMEM EBR blocks by implementing support logic with PFUs. The EBR block facilitates parity checking by supporting an optional parity bit for each data byte. EBR blocks provide byte-enable support for configurations with 18-bit and 36-bit data widths. For more information, refer to ECP5 and ECP5-5G Memory Usage Guide (TN1264).

Table 2.6. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36
True Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18
Pseudo Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36

2.8.2. Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

2.8.3. RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration. By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

2.8.4. Memory Cascading

Larger and deeper blocks of RAM can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

2.8.5. Single, Dual and Pseudo-Dual Port Modes

In all the sysMEM RAM modes the input data and address for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the output.

EBR memory supports the following forms of write behavior for single port or dual port operation:

- **Normal** – Data on the output appears only during a read cycle. During a write cycle, the data (at the current address) does not appear on the output. This mode is supported for all data widths.
- **Write Through** – A copy of the input data appears at the output of the same port during a write cycle. This mode is supported for all data widths.
- **Read-Before-Write** – When new data is written, the old content of the address appears at the output. This mode is supported for x9, x18, and x36 data widths.

2.11. PIO

The PIO contains three blocks: an input register block, output register block, and tristate register block. These blocks contain registers for operating in a variety of modes along with the necessary clock and selection logic.

2.11.1. Input Register Block

The input register blocks for the PIOs on all edges contain delay elements and registers that can be used to condition high-speed interface signals before they are passed to the device core. In addition, the input register blocks for the PIOs on the left and right edges include built-in FIFO logic to interface to DDR and LPDDR memory.

The Input register block on the right and left sides includes gearing logic and registers to implement IDDRX1 and IDDRX2 functions. With two PICs sharing the DDR register path, it can also implement IDDRX71 function used for 7:1 LVDS interfaces. It uses three sets of registers to shift, update, and transfer to implement gearing and the clock domain transfer. The first stage registers samples the high-speed input data by the high-speed edge clock on its rising and falling edges. The second stage registers perform data alignment based on the control signals. The third stage pipeline registers pass the data to the device core synchronized to the low-speed system clock. The top side of the device supports IDDRX1 gearing function. For more information on gearing function, refer to ECP5 and ECP5-5G High-Speed I/O Interface (TN1265).

Figure 2.17 shows the input register block for the PIOs on the top edge.

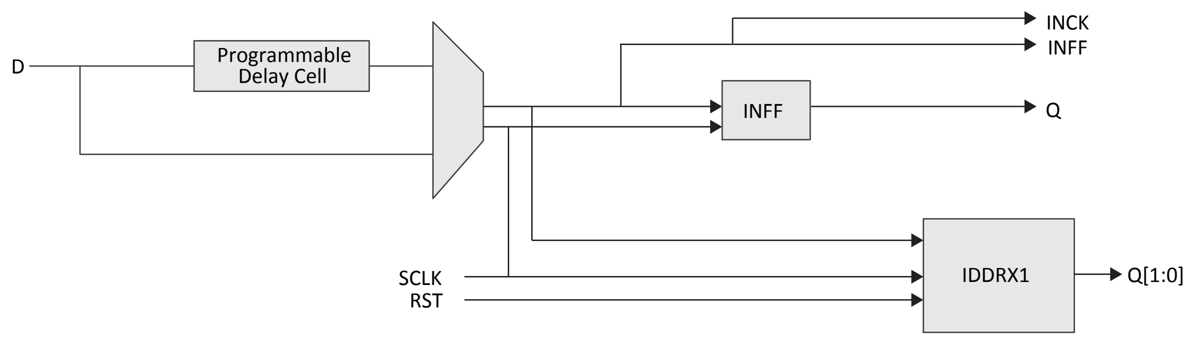


Figure 2.17. Input Register Block for PIO on Top Side of the Device

Figure 2.18 shows the input register block for the PIOs located on the left and right edges.

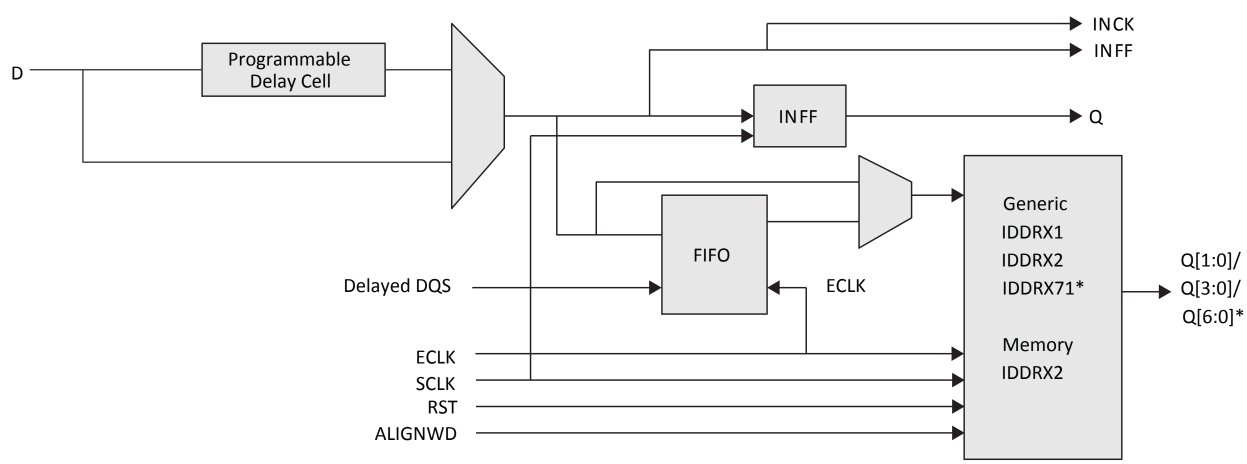


Figure 2.18. Input Register Block for PIO on Left and Right Side of the Device

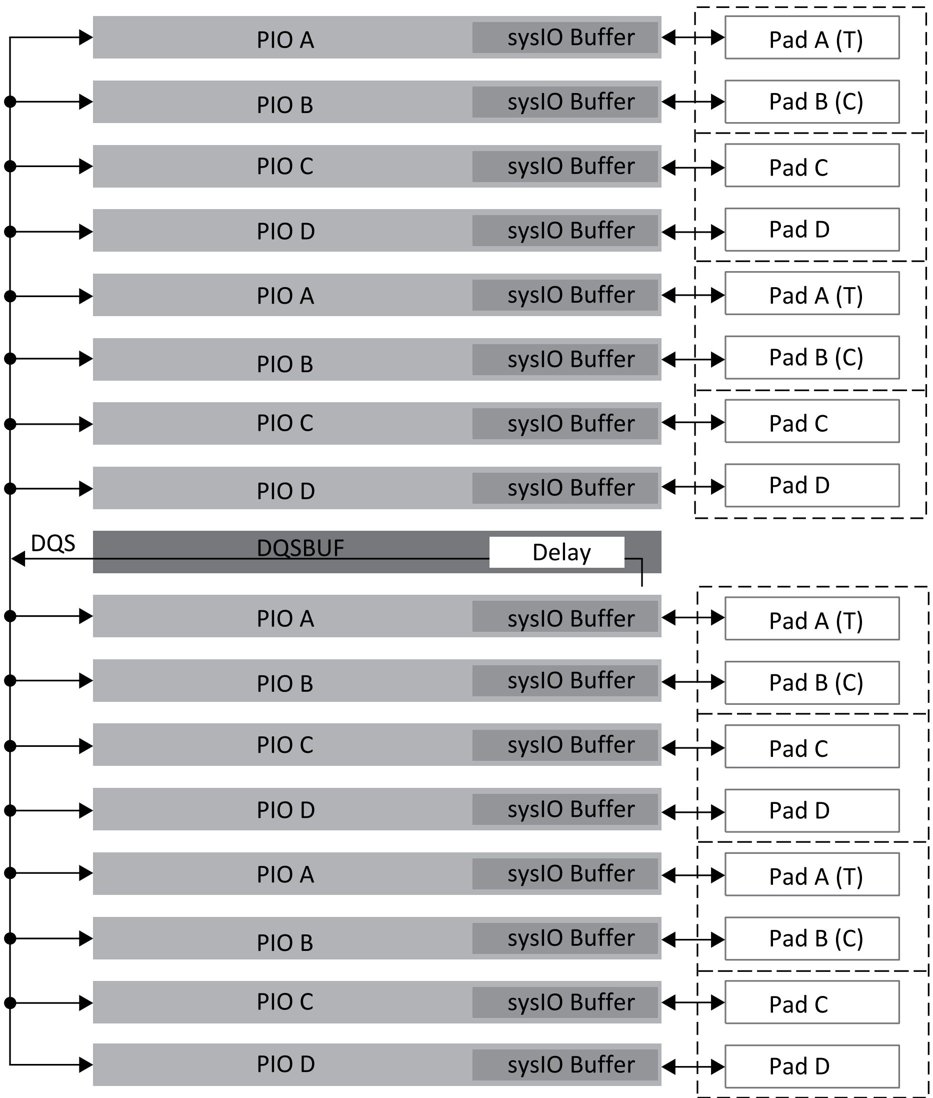


Figure 2.23. DQS Grouping on the Left and Right Edges

2.13.2. DLL Calibrated DQS Delay and Control Block (DQSBUF)

To support DDR memory interfaces (DDR2/3, LPDDR2/3), the DQS strobe signal from the memory must be used to capture the data (DQ) in the PIC registers during memory reads. This signal is output from the DDR memory device aligned to data transitions and must be time shifted before it can be used to capture data in the PIC. This time shifted is achieved by using DQSDEL programmable delay line in the DQS Delay Block (DQS read circuit). The DQSDEL is implemented as a slave delay line and works in conjunction with a master DDRDLL.

This block also includes slave delay line to generate delayed clocks used in the write side to generate DQ and DQS with correct phases within one DQS group. There is a third delay line inside this block used to provide write leveling feature for DDR write if needed.

Each of the read and write side delays can be dynamically shifted using margin control signals that can be controlled by the core logic.

FIFO Control Block shown in Figure 2.24 generates the Read and Write Pointers for the FIFO block inside the Input Register Block. These pointers are generated to control the DQS to ECLK domain crossing using the FIFO module.

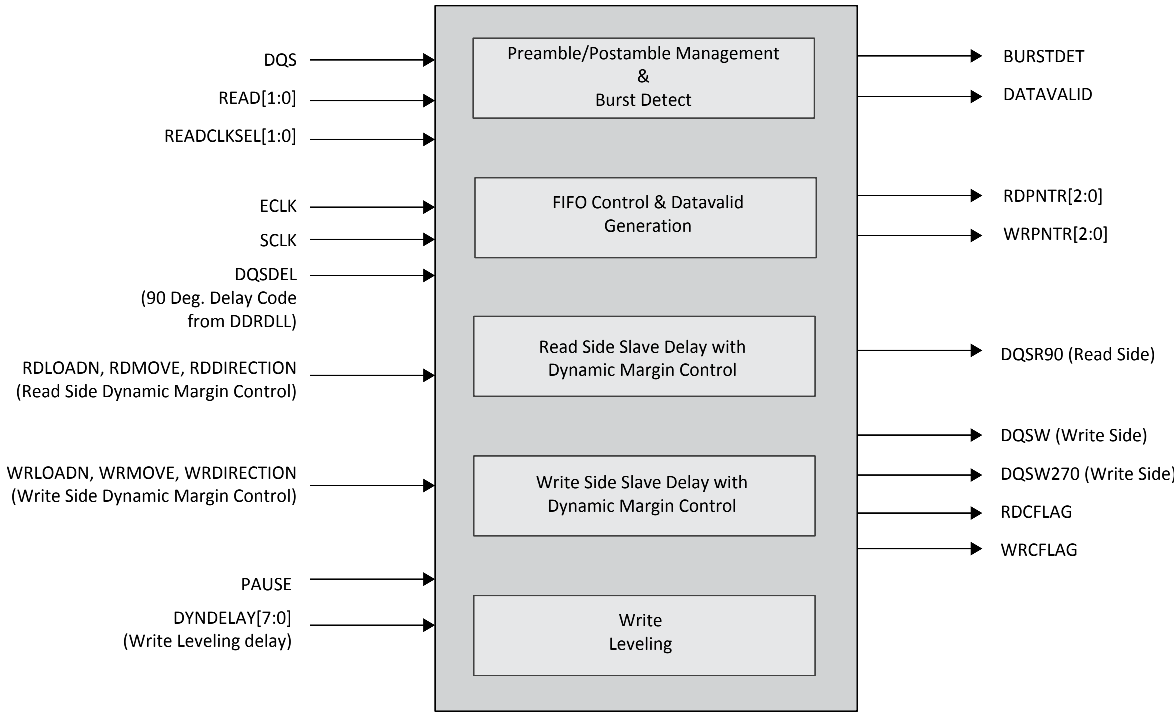


Figure 2.24. DQS Control and Delay Block (DQSBUF)

Table 2.11. DQSBUF Port List Description

Name	Type	Description
DQS	Input	DDR memory DQS strobe
READ[1:0]	Input	Read Input from DDR Controller
READCLKSEL[1:0]	Input	Read pulse selection
SCLK	Input	Slow System Clock
ECLK	Input	High Speed Edge Clock (same frequency as DDR memory)
DQSDEL	Input	90° Delay Code from DDRDLL
RDLOADN, RDMOVE, RDDIRECTION	Input	Dynamic Margin Control ports for Read delay
WRLOADN, WRMOVE, WRDIRECTION	Input	Dynamic Margin Control ports for Write delay
PAUSE	Input	Used by DDR Controller to Pause write side signals during DDRDLL Code update or Write Leveling
DYNDELAY[7:0]	Input	Dynamic Write Leveling Delay Control
DQSR90	Output	90° delay DQS used for Read
DQSW270	Output	90° delay clock used for DQ Write
DQSW	Output	Clock used for DQS Write
RDPNTR[2:0]	Output	Read Pointer for IFIFO module
WRPNTR[2:0]	Output	Write Pointer for IFIFO module
DATAVALID	Output	Signal indicating start of valid data
BURSTDET	Output	Burst Detect indicator
RDFLAG	Output	Read Dynamic Margin Control output to indicate max value
WRFLAG	Output	Write Dynamic Margin Control output to indicate max value

3. DC and Switching Characteristics

3.1. Absolute Maximum Ratings

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Min	Max	Unit
V_{CC}	Supply Voltage	–0.5	1.32	V
V_{CCA}	Supply Voltage	–0.5	1.32	V
V_{CCAUX}, V_{CCAUXA}	Supply Voltage	–0.5	2.75	V
V_{CCIO}	Supply Voltage	–0.5	3.63	V
—	Input or I/O Transient Voltage Applied	–0.5	3.63	V
V_{CCHRX}, V_{CCHTX}	SERDES RX/TX Buffer Supply Voltages	–0.5	1.32	V
—	Voltage Applied on SERDES Pins	–0.5	1.80	V
T_A	Storage Temperature (Ambient)	–65	150	°C
T_J	Junction Temperature	—	+125	°C

Notes:

1. Stress above those listed under the “Absolute Maximum Ratings” may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.
2. Compliance with the Lattice Thermal Management document is required.
3. All voltages referenced to GND.

3.2. Recommended Operating Conditions

Table 3.2. Recommended Operating Conditions

Symbol	Parameter		Min	Max	Unit
V_{CC}[2]	Core Supply Voltage	ECP5	1.045	1.155	V
		ECP5-5G	1.14	1.26	V
V_{CCAUX}[2, 4]	Auxiliary Supply Voltage	—	2.375	2.625	V
V_{CCIO}[2, 3]	I/O Driver Supply Voltage	—	1.14	3.465	V
V_{REF}[1]	Input Reference Voltage	—	0.5	1.0	V
t_{JCOM}	Junction Temperature, Commercial Operation	—	0	85	°C
t_{JIND}	Junction Temperature, Industrial Operation	—	–40	100	°C
SERDES External Power Supply[5]					
V_{CCA}	SERDES Analog Power Supply	ECP5UM	1.045	1.155	V
		ECP5-5G	1.164	1.236	V
V_{CCAUXA}	SERDES Auxiliary Supply Voltage	—	2.374	2.625	V
V_{CCHRX}[6]	SERDES Input Buffer Power Supply	ECP5UM	0.30	1.155	V
		ECP5-5G	0.30	1.26	V
V_{CCHTX}	SERDES Output Buffer Power Supply	ECP5UM	1.045	1.155	V
		ECP5-5G	1.14	1.26	V

Notes:

1. For correct operation, all supplies except V_{REF} must be held in their valid operation range. This is true independent of feature usage.
2. All supplies with same voltage, except SERDES Power Supplies, should be connected together.
3. See recommended voltages by I/O standard in Table 3.4 on page 48.
4. V_{CCAUX} ramp rate must not exceed 30 mV/µs during power-up when transitioning between 0 V and 3 V.
5. Refer to ECP5 and ECP5-5G SERDES/PCS Usage Guide (TN1261) for information on board considerations for SERDES power supplies.
6. V_{CCHRX} is used for Rx termination. It can be biased to Vcm if external AC coupling is used. This voltage needs to meet all the HDin input voltage level requirements specified in the Rx section of this Data Sheet.

3.3. Power Supply Ramp Rates

Table 3.3. Power Supply Ramp Rates

Symbol	Parameter	Min	Typ	Max	Unit
t_{RAMP}	Power Supply ramp rates for all supplies	0.01	—	10	V/ms

Note: Assumes monotonic ramp rates.

3.4. Power-On-Reset Voltage Levels

Table 3.4. Power-On-Reset Voltage Levels

Symbol	Parameter			Min	Typ	Max	Unit
V_{PORUP}	All Devices	Power-On-Reset ramp-up trip point (Monitoring V_{CC}, V_{CCAUX}, and V_{CCIO8})	V_{CC}	0.90	—	1.00	V
			V_{CCAUX}	2.00	—	2.20	V
			V_{CCIO8}	0.95	—	1.06	V
V_{PORDN}	All Devices	Power-On-Reset ramp-down trip point (Monitoring V_{CC}, and V_{CCAUX}	V_{CC}	0.77	—	0.87	V
			V_{CCAUX}	1.80	—	2.00	V

Notes:

- These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.
- Only V_{CCIO8} has a Power-On-Reset ramp up trip point. All other V_{CCIOs} do not have Power-On-Reset ramp up detection.
- V_{CCIO8} does not have a Power-On-Reset ramp down detection. V_{CCIO8} must remain within the Recommended Operating Conditions to ensure proper operation.

3.5. Power up Sequence

Power-On-Reset (POR) puts the ECP5/ECP5-5G device in a reset state. POR is released when V_{CC}, V_{CCAUX}, and V_{CCIO8} are ramped above the V_{PORUP} voltage, as specified above.

V_{CCIO8} controls the voltage on the configuration I/O pins. If the ECP5/ECP5-5G device is using Master SPI mode to download configuration data from external SPI Flash, it is required to ramp V_{CCIO8} above V_{IH} of the external SPI Flash, before at least one of the other two supplies (V_{CC} and/or V_{CCAUX}) is ramped to V_{PORUP} voltage level. If the system cannot meet this power up sequence requirement, and requires the V_{CCIO8} to be ramped last, then the system must keep either PROGRAMN or INITN pin LOW during power up, until V_{CCIO8} reaches V_{IH} of the external SPI Flash. This ensures the signals driven out on the configuration pins to the external SPI Flash meet the V_{IH} voltage requirement of the SPI Flash.

For LFE5UM/LFE5UM5G devices, it is required to power up V_{CCA}, before V_{CCAUXA} is powered up.

3.6. Hot Socketing Specifications

Table 3.5. Hot Socketing Specifications

Symbol	Parameter	Condition	Min	Typ	Max	Unit
IDK_HS	Input or I/O Leakage Current for Top and Bottom Banks Only	$0 \leq V_{IN} \leq V_{IH}$ (Max)	—	—	±1	mA
IDK	Input or I/O Leakage Current for Left and Right Banks Only	$0 \leq V_{IN} < V_{CCIO}$	—	—	±1	mA
		$V_{CCIO} \leq V_{IN} \leq V_{CCIO} + 0.5$ V	—	18	—	mA

Notes:

1. V_{CC}, V_{CCAUX} and V_{CCIO} should rise/fall monotonically.
2. I_{DK} is additive to I_{PU}, I_{PW} or I_{BH}.
3. LVCMOS and LVTTL only.
4. Hot socket specification defines when the hot socketed device's junction temperature is at 85 °C or below. When the hot socketed device's junction temperature is above 85 °C, the I_{DK} current can exceed ±1 mA.

3.12. sysI/O Recommended Operating Conditions

Table 3.11. sysI/O Recommended Operating Conditions

Standard	V_{CCIO}			V_{REF} (V)		
	Min	Typ	Max	Min	Typ	Max
LVCMOS33[1]	3.135	3.3	3.465	—	—	—
LVCMOS33D[3] Output	3.135	3.3	3.465	—	—	—
LVCMOS25[1]	2.375	2.5	2.625	—	—	—
LVCMOS18	1.71	1.8	1.89	—	—	—
LVCMOS15	1.425	1.5	1.575	—	—	—
LVCMOS12[1]	1.14	1.2	1.26	—	—	—
LVTTL33[1]	3.135	3.3	3.465	—	—	—
SSTL15_I, _II[2]	1.43	1.5	1.57	0.68	0.75	0.9
SSTL18_I, _II[2]	1.71	1.8	1.89	0.833	0.9	0.969
SSTL135_I, _II[2]	1.28	1.35	1.42	0.6	0.675	0.75
HSUL12[2]	1.14	1.2	1.26	0.588	0.6	0.612
MIPI D-PHY LP Input[3, 5]	1.425	1.5	1.575	—	—	—
LVDS25[1, 3] Output	2.375	2.5	2.625	—	—	—
subLVS[3] (Input only)	—	—	—	—	—	—
SLVS[3] (Input only)	—	—	—	—	—	—
LVDS25E[3] Output	2.375	2.5	2.625	—	—	—
MLVDS[3] Output	2.375	2.5	2.625	—	—	—
LVPECL33[1, 3] Output	3.135	3.3	3.465	—	—	—
BLVDS25[1, 3] Output	2.375	2.5	2.625	—	—	—
HSULD12D[2, 3]	1.14	1.2	1.26	—	—	—
SSTL135D_I, II[2, 3]	1.28	1.35	1.42	—	—	—
SSTL15D_I, II[2, 3]	1.43	1.5	1.57	—	—	—
SSTL18D_I[1, 2, 3], II[1, 2, 3]	1.71	1.8	1.89	—	—	—

Notes:

1. For input voltage compatibility, refer to ECP5 and ECP5-5G sysIO Usage Guide (TN1262).
2. V_{REF} is required when using Differential SSTL and HSUL to interface to DDR/LPDDR memories.
3. These differential inputs use LVDS input comparator, which uses V_{CCAUX} power
4. All differential inputs and LVDS25 output are supported in the Left and Right banks only. Refer to ECP5 and ECP5-5G sysIO Usage Guide (TN1262) for details.
5. MIPI D-PHY LP input can be implemented by powering VCCIO to 1.5V, and select MIPI LP primitive to meet MIPI Alliance spec on V_{IH} and V_{IL}. It can also be implemented as LVCMOS12 with VCCIO at 1.2V, which would meet V_{IH}/V_{IL} spec on LVCOM12.

3.14.4. LVDS25E

The top and bottom sides of ECP5/ECP5-5G devices support LVDS outputs via emulated complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The scheme shown in Figure 3.1 is one possible solution for point-to-point signals.

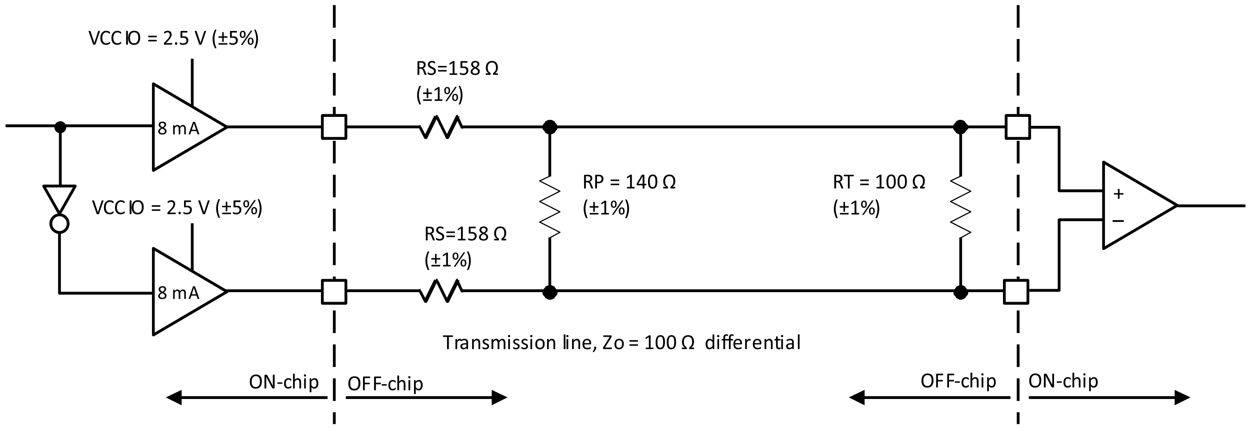


Figure 3.1. LVDS25E Output Termination Example

Table 3.14. LVDS25E DC Conditions

Parameter	Description	Typical	Unit
V_{CCIO}	Output Driver Supply (±5%)	2.50	V
Z_{OUT}	Driver Impedance	20	Ω
R_S	Driver Series Resistor (±1%)	158	Ω
R_P	Driver Parallel Resistor (±1%)	140	Ω
R_T	Receiver Termination (±1%)	100	Ω
V_{OH}	Output High Voltage	1.43	V
V_{OL}	Output Low Voltage	1.07	V
V_{OD}	Output Differential Voltage	0.35	V
V_{CM}	Output Common Mode Voltage	1.25	V
Z_{BACK}	Back Impedance	100.5	Ω
I_{DC}	DC Output Current	6.03	mA

Note: For input buffer, see LVDS Table 3.13 on page 55.

3.18. External Switching Characteristics

Over recommended commercial operating conditions.

Table 3.22. ECP5/ECP5-5G External Switching Characteristics

Parameter	Description	Device	–8		–7		–6		Unit
			Min	Max	Min	Max	Min	Max	
Clocks									
Primary Clock									
f_{MAX_PRI}	Frequency for Primary Clock Tree	—	—	370	—	303	—	257	MHz
t_{W_PRI}	Clock Pulse Width for Primary Clock	—	0.8	—	0.9	—	1.0	—	ns
t_{SKEW_PRI}	Primary Clock Skew within a Device	—	—	420	—	462	—	505	ps
Edge Clock									
f_{MAX_EDGE}	Frequency for Edge Clock Tree	—	—	400	—	350	—	312	MHz
t_{W_EDGE}	Clock Pulse Width for Edge Clock	—	1.175	—	1.344	—	1.50	—	ns
t_{SKEW_EDGE}	Edge Clock Skew within a Bank	—	—	160	—	180	—	200	ps
Generic SDR Input									
General I/O Pin Parameters Using Dedicated Primary Clock Input without PLL									
t_{CO}	Clock to Output - PIO Output Register	All Devices	—	5.4	—	6.1	—	6.8	ns
t_{SU}	Clock to Data Setup - PIO Input Register	All Devices	0	—	0	—	0	—	ns
t_{H}	Clock to Data Hold - PIO Input Register	All Devices	2.7	—	3	—	3.3	—	ns
t_{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	All Devices	1.2	—	1.33	—	1.46	—	ns
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Data Input Delay	All Devices	0	—	0	—	0	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	All Devices	—	400	—	350	—	312	MHz
General I/O Pin Parameters Using Dedicated Primary Clock Input with PLL									
t_{COPLL}	Clock to Output - PIO Output Register	All Devices	—	3.5	—	3.8	—	4.1	ns
t_{SUPLL}	Clock to Data Setup - PIO Input Register	All Devices	0.7	—	0.78	—	0.85	—	ns
t_{HPLL}	Clock to Data Hold - PIO Input Register	All Devices	0.8	—	0.89	—	0.98	—	ns
t_{SU_DELPLL}	Clock to Data Setup - PIO Input Register with Data Input Delay	All Devices	1.6	—	1.78	—	1.95	—	ns

3.19. sysCLOCK PLL Timing

Over recommended operating conditions.

Table 3.23. sysCLOCK PLL Timing

Parameter	Descriptions	Conditions	Min	Max	Units
f_{IN}	Input Clock Frequency (CLKI, CLKFB)	—	8	400	MHz
f_{OUT}	Output Clock Frequency (CLKOP, CLKOS)	—	3.125	400	MHz
f_{VCO}	PLL VCO Frequency	—	400	800	MHz
f_{PFD}[3]	Phase Detector Input Frequency	—	10	400	MHz
AC Characteristics					
t_{DT}	Output Clock Duty Cycle	—	45	55	%
t_{PH4}	Output Phase Accuracy	—	–5	5	%
t_{OPJIT}[1]	Output Clock Period Jitter	$f_{OUT} \geq 100$ MHz	—	100	ps p-p
		$f_{OUT} < 100$ MHz	—	0.025	UIPP
	Output Clock Cycle-to-Cycle Jitter	$f_{OUT} \geq 100$ MHz	—	200	ps p-p
		$f_{OUT} < 100$ MHz	—	0.050	UIPP
	Output Clock Phase Jitter	$f_{PFD} \geq 100$ MHz	—	200	ps p-p
		$f_{PFD} < 100$ MHz	—	0.011	UIPP
t_{SPO}	Static Phase Offset	Divider ratio = integer	—	400	ps p-p
t_W	Output Clock Pulse Width	At 90% or 10%	0.9	—	ns
t_{LOCK}[2]	PLL Lock-in Time	—	—	15	ms
t_{UNLOCK}	PLL Unlock Time	—	—	50	ns
t_{IPJIT}	Input Clock Period Jitter	$f_{PFD} \geq 20$ MHz	—	1,000	ps p-p
		$f_{PFD} < 20$ MHz	—	0.02	UIPP
t_{HI}	Input Clock High Time	90% to 90%	0.5	—	ns
t_{LO}	Input Clock Low Time	10% to 10%	0.5	—	ns
t_{RST}	RST/ Pulse Width	—	1	—	ms
t_{RSTREC}	RST Recovery Time	—	1	—	ns
t_{LOAD_REG}	Min Pulse for CIB_LOAD_REG	—	10	—	ns
$t_{ROTATE-SETUP}$	Min time for CIB dynamic phase controls to be stable fore CIB_ROTATE	—	5	—	ns
$t_{ROTATE-WD}$	Min pulse width for CIB_ROTATE to maintain “0” or	—	4	—	VCO cycles

Notes:

1. Jitter sample is taken over 10,000 samples for Periodic jitter, and 2,000 samples for Cycle-to-Cycle jitter of the primary PLL output with clean reference clock with no additional I/O toggling.
2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.
3. Period jitter and cycle-to-cycle jitter numbers are guaranteed for $f_{PFD} > 10$ MHz. For $f_{PFD} < 10$ MHz, the jitter numbers may not be met in certain conditions.

3.21. SERDES/PCS Block Latency

Table 3.26 describes the latency of each functional block in the transmitter and receiver. Latency is given in parallel clock cycles. Figure 3.13 shows the location of each block.

Table 3.26. SERDES/PCS Latency Breakdown

Item	Description	Min	Avg	Max	Fixed	Bypass	Unit[3]
Transmit Data Latency[1]							
T1	FPGA Bridge - Gearing disabled with same clocks	3	—	4	—	1	byte clk
	FPGA Bridge - Gearing enabled	5	—	7	—	—	word clk
T2	8b10b Encoder	—	—	—	2	1	byte clk
T3	SERDES Bridge transmit	—	—	—	2	1	byte clk
T4	Serializer: 8-bit mode	—	—	—	15 + Δ1	—	UI + ps
	Serializer: 10-bit mode	—	—	—	18 + Δ1	—	UI + ps
T5	Pre-emphasis ON	—	—	—	1 + Δ2	—	UI + ps
	Pre-emphasis OFF	—	—	—	0 + Δ3	—	UI + ps
Receive Data Latency[2]							
R1	Equalization ON	—	—	—	Δ1	—	UI + ps
	Equalization OFF	—	—	—	Δ2	—	UI + ps
R2	Deserializer: 8-bit mode	—	—	—	10 + Δ3	—	UI + ps
	Deserializer: 10-bit mode	—	—	—	12 + Δ3	—	UI + ps
R3	SERDES Bridge receive	—	—	—	2	—	byte clk
R4	Word alignment	3.1	—	4	—	1	byte clk
R5	8b10b decoder	—	—	—	1	0	byte clk
R6	Clock Tolerance Compensation	7	15	23	—	1	byte clk
R7	FPGA Bridge - Gearing disabled with same clocks	4	—	5	—	1	byte clk
	FPGA Bridge - Gearing enabled	7	—	9	—	—	word clk

Notes:

1. Δ1 = –245 ps, Δ2 = +88 ps, Δ3 = +112 ps.
2. Δ1 = +118 ps, Δ2 = +132 ps, Δ3 = +700 ps.
3. byte clk = 8UIs (8-bit mode), or 10 UIs (10-bit mode); word clk = 16UIs (8-bit mode), or 20 UIs (10-bit mode).

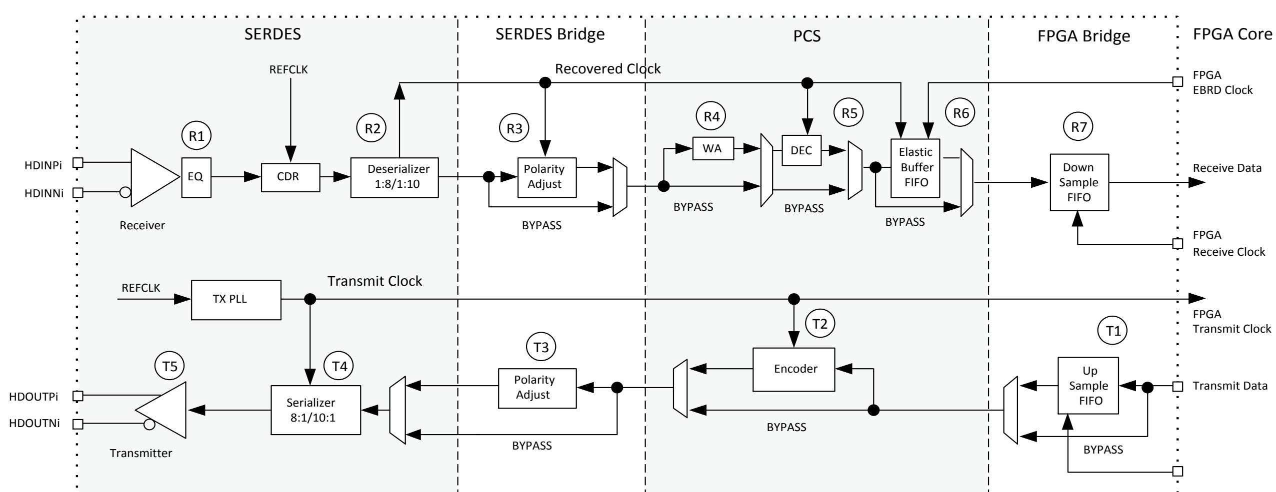


Figure 3.13. Transmitter and Receiver Latency Block Diagram

Table 3.44. Test Fixture Required Components, Non-Terminated Interfaces

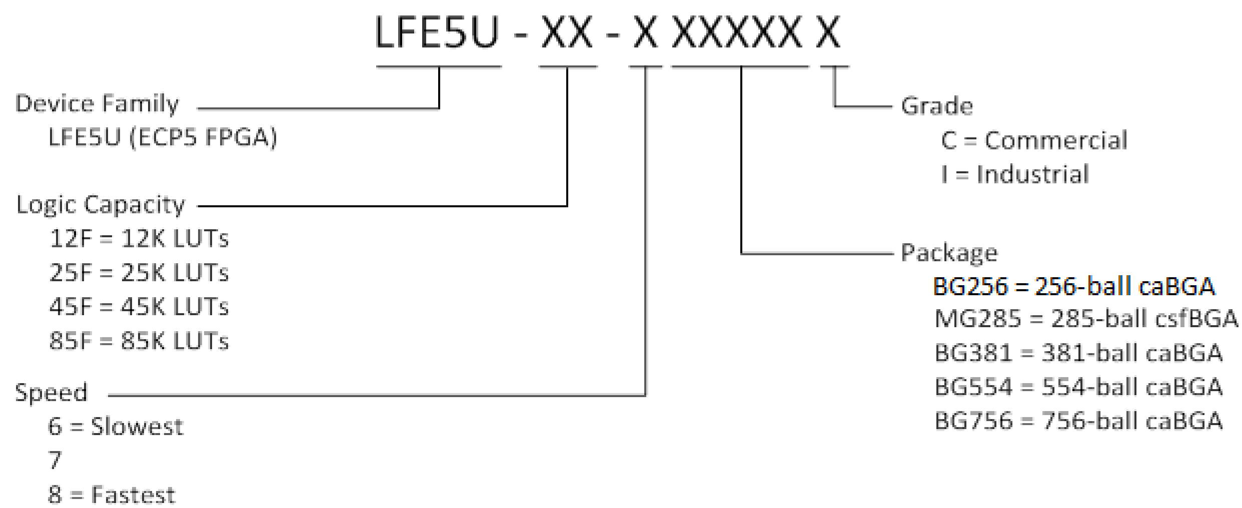
Test Condition	R_1	R_2	C_L	Timing Ref.	V_T
LVTTL and other LVCMOS settings (L ≥ H, H ≥ L)	∞	∞	0 pF	LVCMOS 3.3 = 1.5 V	—
				LVCMOS 2.5 = $V_{CCIO}/2$	—
				LVCMOS 1.8 = $V_{CCIO}/2$	—
				LVCMOS 1.5 = $V_{CCIO}/2$	—
				LVCMOS 1.2 = $V_{CCIO}/2$	—
LVCMOS 2.5 I/O (Z ≥ H)	∞	1 MΩ	0 pF	$V_{CCIO}/2$	—
LVCMOS 2.5 I/O (Z ≥ L)	1 MΩ	∞	0 pF	$V_{CCIO}/2$	V_{CCIO}
LVCMOS 2.5 I/O (H ≥ Z)	∞	100	0 pF	V_{OH} – 0.10	—
LVCMOS 2.5 I/O (L ≥ Z)	100	∞	0 pF	V_{OL} + 0.10	V_{CCIO}

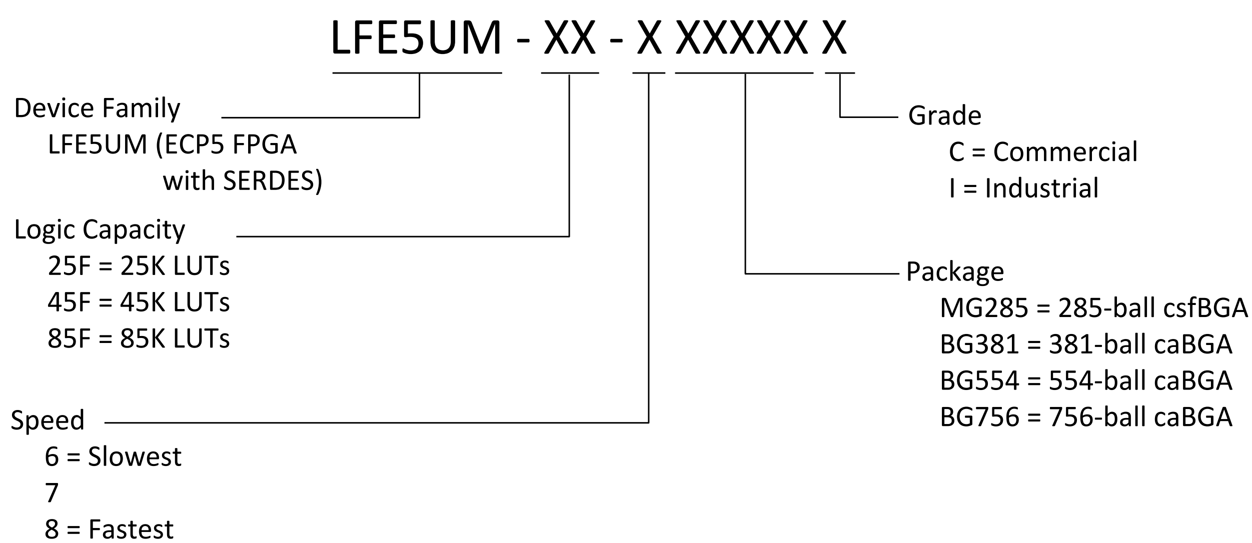
Note: Output test conditions for all other interfaces are determined by the respective standards.

Signal Name	I/O	Description
PLL, DLL and Clock Functions *(Continued)*		
[L/R]DQS[group_num]	I/O	DQS input/output pads: T (top), R (right), group_ num = ball number associated with DQS[T] pin.
[T/R]]DQ[group_num]	I/O	DQ input/output pads: T (top), R (right), group_ num = ball number associated with DQS[T] pin.
Test and Programming (Dedicated Pins)		
TMS	I	Test Mode Select input, used to control the 1149.1 state machine. Pull-up is enabled during configuration. This is a dedicated input pin.
TCK	I	Test Clock input pin, used to clock the 1149.1 state machine. No pull-up enabled. This is a dedicated input pin.
TDI	I	Test Data in pin. Used to load data into device using 1149.1 state machine. After power-up, this TAP port can be activated for configuration by sending appropriate command. (Note: once a configuration port is selected it is locked. Another configuration port cannot be selected until the power-up sequence). Pull-up is enabled during configuration. This is a dedicated input pin.
TDO	O	Output pin. Test Data Out pin used to shift data out of a device using 1149.1. This is a dedicated output pin.
Configuration Pads (Used during sysCONFIG)		
CFG[2:0]	I	Mode pins used to specify configuration mode values latched on rising edge of INITN. During configuration, a pull-up is enabled. These are dedicated pins.
INITN	I/O	Open Drain pin. Indicates the FPGA is ready to be configured. During configuration, a pull-up is enabled. This is a dedicated pin.
PROGRAMN	I	Initiates configuration sequence when asserted low. This pin always has an active pull-up. This is a dedicated pin.
DONE	I/O	Open Drain pin. Indicates that the configuration sequence is complete, and the startup sequence is in progress. This is a dedicated pin.
CCLK	I/O	Input Configuration Clock for configuring an FPGA in Slave SPI, Serial, and CPU modes. Output Configuration Clock for configuring an FPGA in Master configuration modes (Master SPI, Master Serial). This is a dedicated pin.
HOLDN/DI/BUSY/CSSPIN/CEN	I/O	Parallel configuration mode busy indicator. SPI/SPIm mode data output. This is a shared I/O pin. This is a shared I/O pin. When not in configuration, it can be used as general purpose I/O pin.
CSN/SN	I/O	Parallel configuration mode active-low chip select. Slave SPI chip select. This is a shared I/O pin. When not in configuration, it can be used as general purpose I/O pin.
CS1N	I	Parallel configuration mode active-low chip select. This is a shared I/O pin. When not in configuration, it can be used as general purpose I/O pin.
WRITEN	I	Write enable for parallel configuration modes. This is a shared I/O pin. When not in configuration, it can be used as general purpose I/O pin.
DOUT/CSON	O	Serial data output. Chip select output. SPI/SPIm mode chip select. This is a shared I/O pin. When not in configuration, it can be used as general purpose I/O
D0/MOSI/IO0	I/O	Parallel configuration I/O. Open drain during configuration. When in SPI modes, it is an output in Master mode, and input in Slave mode. This is a shared I/O pin. When not in configuration, it can be used as general purpose I/O pin.

5. Ordering Information

5.1. ECP5/ECP5-5G Part Number Description





LFE5UM5G - XX - X XXXXX X

Device Family
LFE5UM5G (ECP5-5G FPGA with SERDES)

Logic Capacity
25F = 25K LUTs
45F = 45K LUTs
85F = 85K LUTs

Speed
8 = Fastest

Grade
C = Commercial
I = Industrial

Package
MG285 = 285-ball csfBGA
BG381 = 381-ball caBGA
BG554 = 554-ball caBGA
BG756 = 756-ball caBGA

5.2. Ordering Part Numbers

5.2.1. Commercial

Part number	Grade	Package	Pins	Temp.	LUTs (K)	SERDES
LFE5U-12F-6BG256C	–6	Lead free caBGA	256	Commercial	12	No
LFE5U-12F-7BG256C	–7	Lead free caBGA	256	Commercial	12	No
LFE5U-12F-8BG256C	–8	Lead free caBGA	256	Commercial	12	No
LFE5U-12F-6MG285C	–6	Lead free csfBGA	285	Commercial	12	No
LFE5U-12F-7MG285C	–7	Lead free csfBGA	285	Commercial	12	No
LFE5U-12F-8MG285C	–8	Lead free csfBGA	285	Commercial	12	No
LFE5U-12F-6BG381C	–6	Lead free caBGA	381	Commercial	12	No
LFE5U-12F-7BG381C	–7	Lead free caBGA	381	Commercial	12	No
LFE5U-12F-8BG381C	–8	Lead free caBGA	381	Commercial	12	No
LFE5U-25F-6BG256C	–6	Lead free caBGA	256	Commercial	24	No
LFE5U-25F-7BG256C	–7	Lead free caBGA	256	Commercial	24	No
LFE5U-25F-8BG256C	–8	Lead free caBGA	256	Commercial	24	No
LFE5U-25F-6MG285C	–6	Lead free csfBGA	285	Commercial	24	No
LFE5U-25F-7MG285C	–7	Lead free csfBGA	285	Commercial	24	No
LFE5U-25F-8MG285C	–8	Lead free csfBGA	285	Commercial	24	No
LFE5U-25F-6BG381C	–6	Lead free caBGA	381	Commercial	24	No
LFE5U-25F-7BG381C	–7	Lead free caBGA	381	Commercial	24	No
LFE5U-25F-8BG381C	–8	Lead free caBGA	381	Commercial	24	No
LFE5U-45F-6BG256C	–6	Lead free caBGA	256	Commercial	44	No
LFE5U-45F-7BG256C	–7	Lead free caBGA	256	Commercial	44	No
LFE5U-45F-8BG256C	–8	Lead free caBGA	256	Commercial	44	No
LFE5U-45F-6MG285C	–6	Lead free csfBGA	285	Commercial	44	No
LFE5U-45F-7MG285C	–7	Lead free csfBGA	285	Commercial	44	No
LFE5U-45F-8MG285C	–8	Lead free csfBGA	285	Commercial	44	No
LFE5U-45F-6BG381C	–6	Lead free caBGA	381	Commercial	44	No
LFE5U-45F-7BG381C	–7	Lead free caBGA	381	Commercial	44	No
LFE5U-45F-8BG381C	–8	Lead free caBGA	381	Commercial	44	No
LFE5U-45F-6BG554C	–6	Lead free caBGA	554	Commercial	44	No
LFE5U-45F-7BG554C	–7	Lead free caBGA	554	Commercial	44	No

Part number	Grade	Package	Pins	Temp.	LUTs (K)	SERDES
LFE5U-85F-6BG756I	–6	Lead free caBGA	756	Industrial	84	No
LFE5U-85F-7BG756I	–7	Lead free caBGA	756	Industrial	84	No
LFE5U-85F-8BG756I	–8	Lead free caBGA	756	Industrial	84	No
LFE5UM-25F-6MG285I	–6	Lead free csfBGA	285	Industrial	24	Yes
LFE5UM-25F-7MG285I	–7	Lead free csfBGA	285	Industrial	24	Yes
LFE5UM-25F-8MG285I	–8	Lead free csfBGA	285	Industrial	24	Yes
LFE5UM-25F-6BG381I	–6	Lead free caBGA	381	Industrial	24	Yes
LFE5UM-25F-7BG381I	–7	Lead free caBGA	381	Industrial	24	Yes
LFE5UM-25F-8BG381I	–8	Lead free caBGA	381	Industrial	24	Yes
LFE5UM-45F-6MG285I	–6	Lead free csfBGA	285	Industrial	44	Yes
LFE5UM-45F-7MG285I	–7	Lead free csfBGA	285	Industrial	44	Yes
LFE5UM-45F-8MG285I	–8	Lead free csfBGA	285	Industrial	44	Yes
LFE5UM-45F-6BG381I	–6	Lead free caBGA	381	Industrial	44	Yes
LFE5UM-45F-7BG381I	–7	Lead free caBGA	381	Industrial	44	Yes
LFE5UM-45F-8BG381I	–8	Lead free caBGA	381	Industrial	44	Yes
LFE5UM-45F-6BG554I	–6	Lead free caBGA	554	Industrial	44	Yes
LFE5UM-45F-7BG554I	–7	Lead free caBGA	554	Industrial	44	Yes
LFE5UM-45F-8BG554I	–8	Lead free caBGA	554	Industrial	44	Yes
LFE5UM-85F-6MG285I	–6	Lead free csfBGA	285	Industrial	84	Yes
LFE5UM-85F-7MG285I	–7	Lead free csfBGA	285	Industrial	84	Yes
LFE5UM-85F-8MG285I	–8	Lead free csfBGA	285	Industrial	84	Yes
LFE5UM-85F-6BG381I	–6	Lead free caBGA	381	Industrial	84	Yes
LFE5UM-85F-7BG381I	–7	Lead free caBGA	381	Industrial	84	Yes
LFE5UM-85F-8BG381I	–8	Lead free caBGA	381	Industrial	84	Yes
LFE5UM-85F-6BG554I	–6	Lead free caBGA	554	Industrial	84	Yes
LFE5UM-85F-7BG554I	–7	Lead free caBGA	554	Industrial	84	Yes
LFE5UM-85F-8BG554I	–8	Lead free caBGA	554	Industrial	84	Yes
LFE5UM-85F-6BG756I	–6	Lead free caBGA	756	Industrial	84	Yes
LFE5UM-85F-7BG756I	–7	Lead free caBGA	756	Industrial	84	Yes
LFE5UM-85F-8BG756I	–8	Lead free caBGA	756	Industrial	84	Yes
LFE5UM5G-25F-8MG285I	–8	Lead free csfBGA	285	Industrial	24	Yes
LFE5UM5G-25F-8BG381I	–8	Lead free caBGA	381	Industrial	24	Yes
LFE5UM5G-45F-8MG285I	–8	Lead free csfBGA	285	Industrial	44	Yes
LFE5UM5G-45F-8BG381I	–8	Lead free caBGA	381	Industrial	44	Yes
LFE5UM5G-45F-8BG554I	–8	Lead free caBGA	554	Industrial	44	Yes
LFE5UM5G-85F-8MG285I	–8	Lead free csfBGA	285	Industrial	84	Yes
LFE5UM5G-85F-8BG381I	–8	Lead free caBGA	381	Industrial	84	Yes
LFE5UM5G-85F-8BG554I	–8	Lead free caBGA	554	Industrial	84	Yes
LFE5UM5G-85F-8BG756I	–8	Lead free caBGA	756	Industrial	84	Yes

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